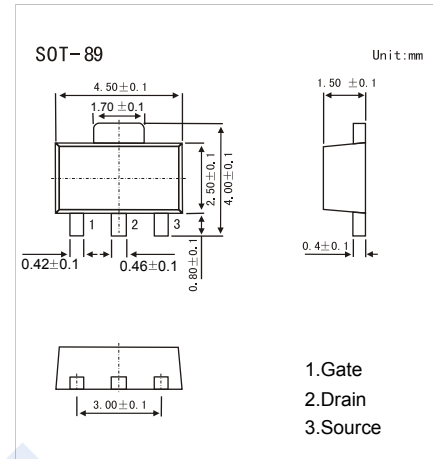
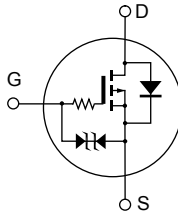


P-Channel MOSFET

2SJ244

■ Features

- $V_{DS} (V) = -12V$
- $I_D = -2 A$
- $R_{DS(ON)} < 0.8 \Omega$ ($V_{GS} = -4V$)
- $R_{DS(ON)} < 0.9 \Omega$ ($V_{GS} = -2.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	± 7	
Continuous Drain Current	I_D	-2	A
Pulsed Drain Current (Note.1)	I_{DM}	-4	
Power Dissipation	P_D	1	W
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10 \mu s$, duty cycle $\leq 10\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -1mA, V_{GS} = 0V$	-12			V
Gate-Source Breakdown Voltage	V_{GSS}	$I_G = \pm 10 \mu A, V_{DS} = 0V$	± 7			
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -8V, V_{GS} = 0V$			-1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 6V$			± 5	μA
Gate to Source Cutoff Voltage	$V_{GS(off)}$	$V_{GS} = -5V, I_D = -100\mu A$	-0.4		-1.4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4V, I_D = -1A$			0.8	Ω
		$V_{GS} = -2.5V, I_D = -0.5A$			0.9	
Forward Transconductance	g_{FS}	$V_{DS} = -5V, I_D = -1A$		1.8		S
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -5V, f = 1MHz$		130		pF
Output Capacitance	C_{oss}			50		
Reverse Transfer Capacitance	C_{rss}			260		
Turn-On DelayTime	$t_{d(on)}$		$V_{GS(on)} = -4V, I_D = -0.2A, R_L = 51 \Omega$		365	
Turn-Off DelayTime	$t_{d(off)}$			1450		
Diode Forward Voltage	V_{SD}	$I_S = -4A, V_{GS} = 0V$			-7	V

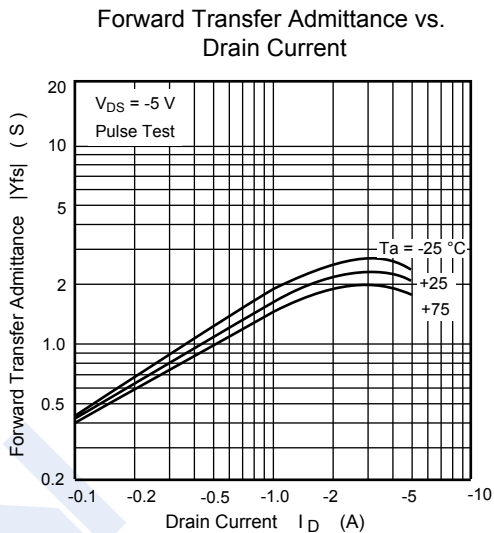
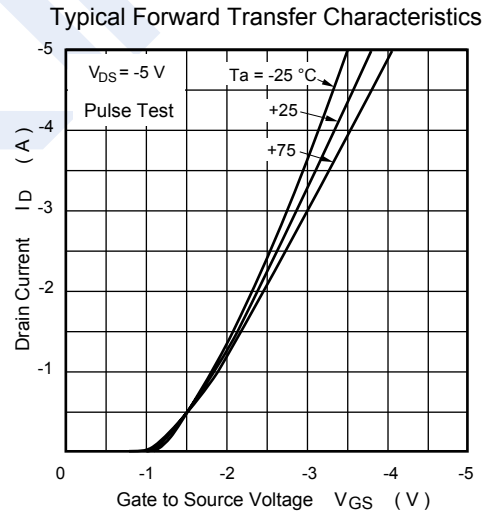
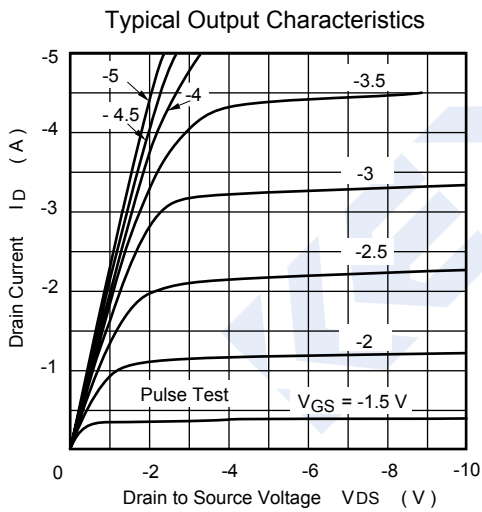
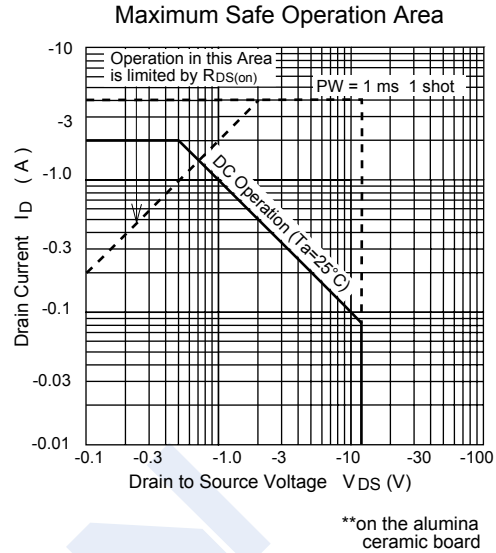
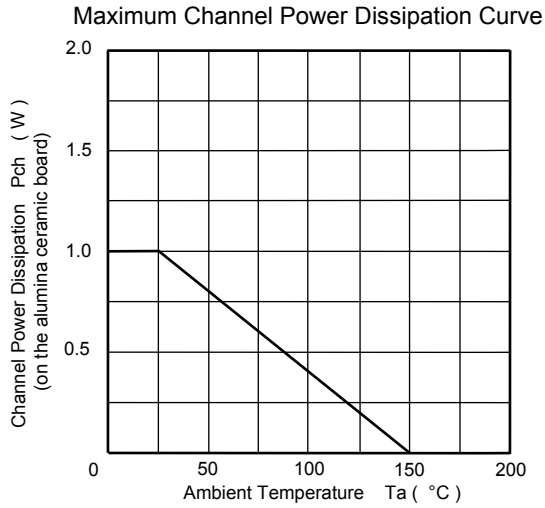
■ Marking

Marking	JY
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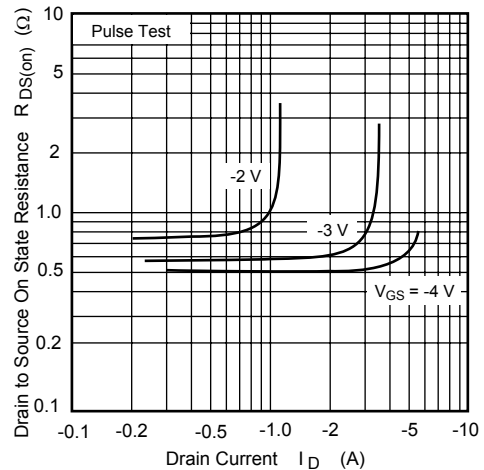
P-Channel MOSFET

2SJ244

■ Typical Characteristics



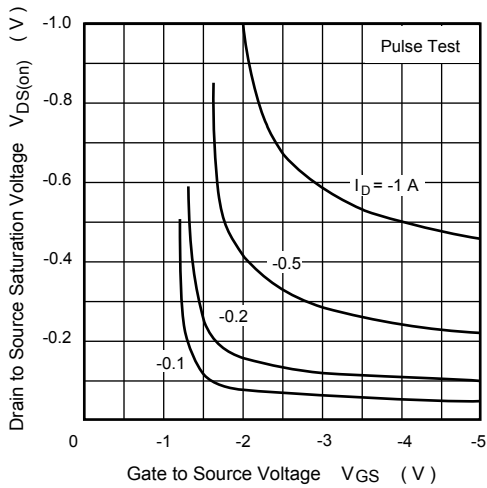
Drain to Source on State Resistance vs. Drain Current



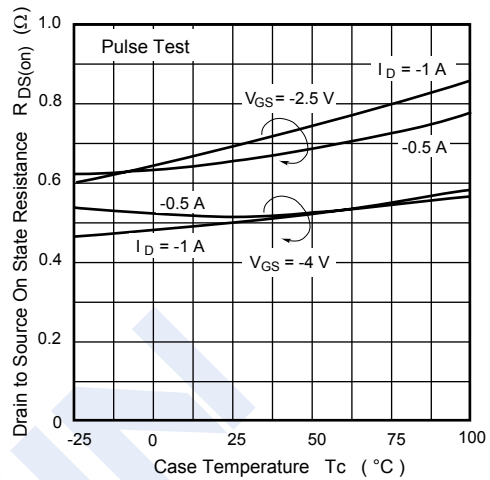
P-Channel MOSFET 2SJ244

■ Typical Characteristics

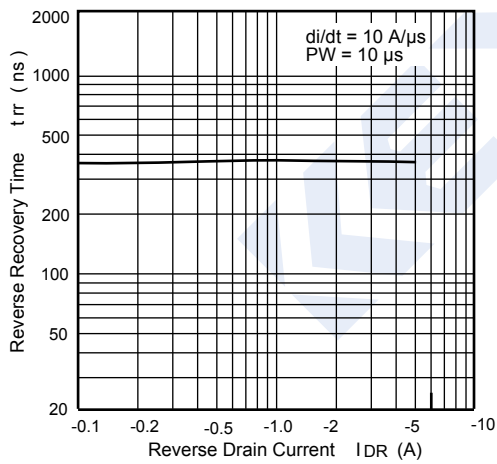
Drain to Source Saturation Voltage vs. Gate to Source Voltage



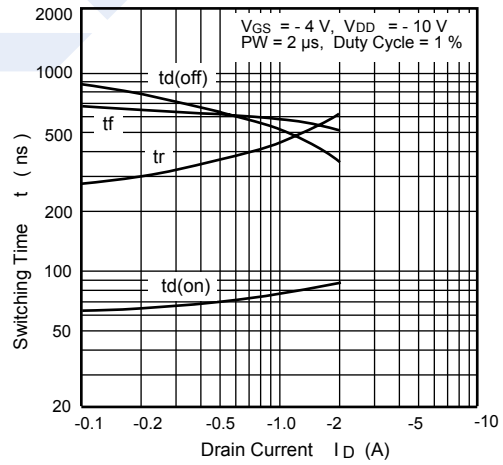
Drain to Source on State Resistance vs. Case Temperature



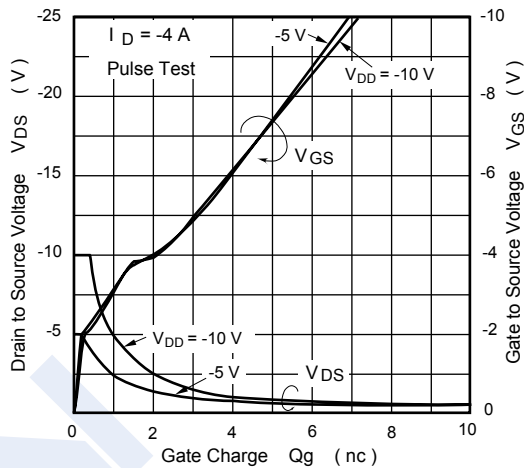
Reverse Recovery Time vs. Reverse Drain Current



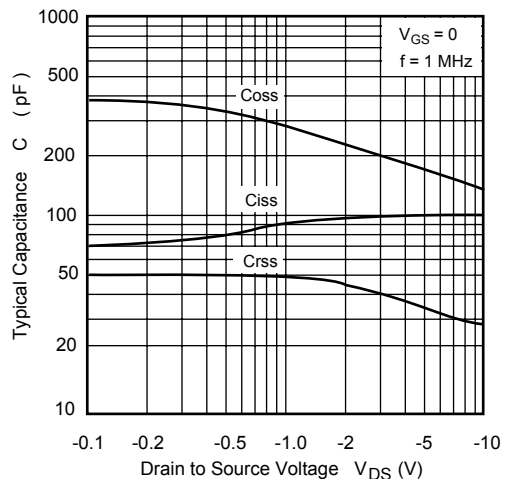
Switching Time vs. Drain Current



Dynamic Input Characteristics



Typical Capacitance vs. Drain to Source Voltage



P-Channel MOSFET

2SJ244

■ Typical Characteristics

Reverse Drain Current vs.
Source to Drain Voltage

